

**REMARKS**

Claims 1-10 are pending in this application of which claims 1 has been amended and claim 10 is newly-added.

In the Office Action of November 5, 2003, claims 1-4 and 6-8 were rejected under 35 USC §103(a) are unpatentable over Huang et al. in view of Chang.

Applicants respectively traverse this rejection.

As noted in Applicants' previous response of August 19, 2002, Huang et al. discloses a method of forming a grooved fuse (plug fuse) in the same step that via plugs are formed in the guard ring area 14 and in product device areas. The groove is provided to alleviate the stress which is applied to the pad and would propagate therefrom to the line conductor during bonding of the wire to the pad. Key guard rings are formed around the plug guise. A semiconductor structure is provided having a fuse area, a guard ring area surrounding the fuse area, and a device area. First and second conductive strips are formed. First and second insulating layers are formed over the first and second conductive strips. Plug contacts and fuse plugs are formed through the first and second insulating layers to the first and second conductive strips. A third insulating layer is formed over the second insulating layer. Metal lines are formed over the third insulating layer in the device area. A fuse via opening is formed in the third insulating layer. A plug fuse is formed in the fuse via opening. A fourth insulating layer is formed over the plug fuse and the third insulating layer. A fuse opening is formed at least partially through the fourth insulating layer over the fuse area.

Fig. 5 shows pads 72 provided on the upper most interlayer insulation film 66, where the pads 72 are separated by the groove. Huang et al. fails to show a line conductor, distinct from the pad, on an upper surface of the upper most interlayer insulation film 66. Although third plug ring 68 may be considered a line conductor, it is arranged within the upper most interlayer insulation film 66, not on the upper surface, as in the present invention.

The Examiner continues to urge that the cross-sections 72 in Fig. 5 of Huang et al. are a line conductor and a pad, respectively. However, each of the cross-sections 72 is a portion of a ring-shaped pattern and is the upper-most metal layer forming guard ring 74 as shown in Fig. 6 of Huang et al. Thus, the cross-sections 72 in Fig. 5 of Huang et al. are not separated each other but instead form a single body.

If the cross-section 72 in the right-hand side is a line conductor, the cross-section 72 in the left-hand side is also a line conductor and cannot be a pad.

Fuse window 84 in Huang et al., which is regarded by the Examiner as corresponding to the groove in the present invention, is formed in the insulating layer in the area inside the ring-shaped pattern. Hence, the fuse window 84 should be a groove formed between line conductors or between pads. The fuse window 84 is provided for facilitating the cutting of plug fuse 58B by irradiation of a laser beam applied thereto through fuse window 84. Thus, such a groove as fuse window 84 does not teach the effect of the groove in the present invention in which the groove alleviates the stress propagating from the pad to the line conductor, when it is applied to the pad during the wire bonding to the pad.

The Examiner has also admitted that Huang et al. does not disclose that pad 72 is on the upper surface of insulating film 76, but has cited Chang for teaching this feature.

Applicants respectfully disagree. Chang discloses a method for making a multi-level antifuse structure, in which a third conductive layer 48 is disclosed.

Column 5, lines 15-20 disclose:

The third conductive layer 48 is, again, preferably a sandwich of TiW, Al and TiW. The third conductive layer 48 is preferably patterned by conventional photolithography techniques to form conductive lines which couple the antifuse structure 28 of the present invention to other circuit elements of the integrated circuit.

Thus, although Chang can be said to teach conductive lines on the upper structure of the antifuse structure, there is no suggestion of a pad being provided on the upper surface of a most upper one of the interlayer insulation film, as recited in claim 1 of the instant application.

Chang discloses an "antifuse structure", and not a "fuse structure". Antifuse layers 36 and 42 in Fig. 2 of Chang are formed of amorphous silicon (A-Si) and have high resistance (1 gigaohms, for example), and conductive paths of low resistance such as 20 to 100 ohms are established for a current flowing in vertical direction (in the direction along thickness of the layers). Thus, it is apparent that the technology of Chang is different from that of Huang et al., and only the term "fuse" is common between Chang and Huang et al.

Chang discloses third conductive layer 48 formed on the top surface of an insulating layer, which is no more than a wiring means for supplying currents to antifuse layers 36 and 42 through conductive via 46 and is electrically connected to another peripheral circuit. (See the plan view of

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Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP



William L. Brooks  
Attorney for Applicants  
Reg. No. 34,129

WLB/anp  
Atty. Docket No. 020129  
Suite 1000  
1725 K Street, N.W.  
Washington, D.C. 20006  
(202) 659-2930



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PATENT TRADEMARK OFFICE

Enclosures: Request for Continued Examination  
Petition For Extension of Time

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